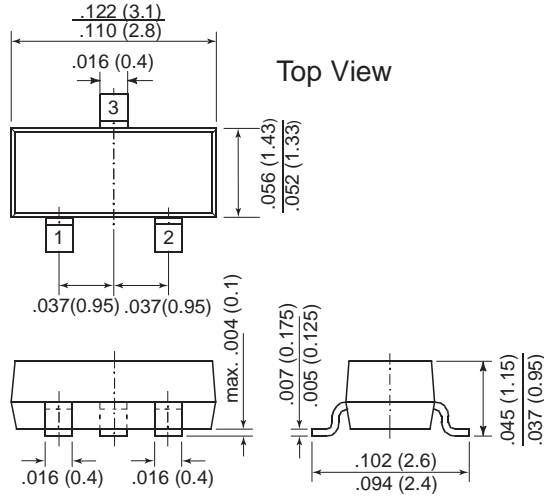


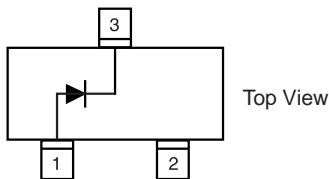
## Small-Signal Diode


**TO-236AB (SOT-23)**


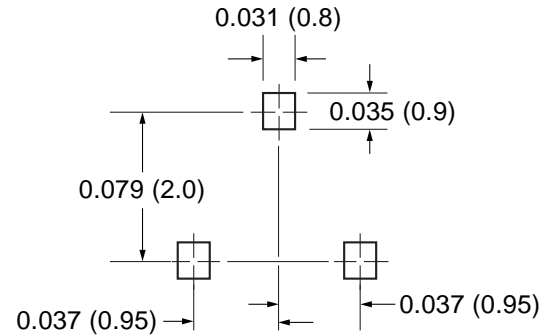
Dimensions in inches and (millimeters)

### Marking

A2



### Mounting Pad Layout



### Features

- Silicon Epitaxial Planar Diodes
- Fast switching diode in case SOT-23, especially suited for automatic insertion.
- This diodes are also available in other case styles including: the DO-35 case with the type designation 1N4148, the Mini-MELF case with the type designation LL4148, and the SOD-123 case with the type designation 1N4148W.

### Mechanical Data

**Case:** SOT-23 Plastic Package

**Weight:** approx. 0.008g

**Packaging Codes/Options:**

E8/10K per 13" reel (8mm tape), 30K/box

E9/3K per 7" reel (8mm tape), 30K/box

### Maximum Ratings and Thermal Characteristics (T<sub>A</sub> = 25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Reverse Voltage	V <sub>R</sub>	75	V
Peak Reverse Voltage	V <sub>RM</sub>	100	V
Rectified Current (Average) Half Wave Rectification with Resist. Load at T <sub>amb</sub> = 25°C and ≥ f ≥ 50Hz	I <sub>F(AV)</sub>	150 <sup>(1)</sup>	mA
Surge Forward Current at t < 1s and T <sub>j</sub> = 25°C	I <sub>FSM</sub>	500	mA
Power Dissipation up to T <sub>amb</sub> = 25°C	P <sub>tot</sub>	350 <sup>(1)</sup>	mW
Thermal Resistance Junction to Ambient Air	R <sub>θJA</sub>	450 <sup>(1)</sup>	°C/W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature Range	T <sub>s</sub>	-65 to +150	°C

**Note:**

(1) Device on fiberglass substrate, see layout on next page.

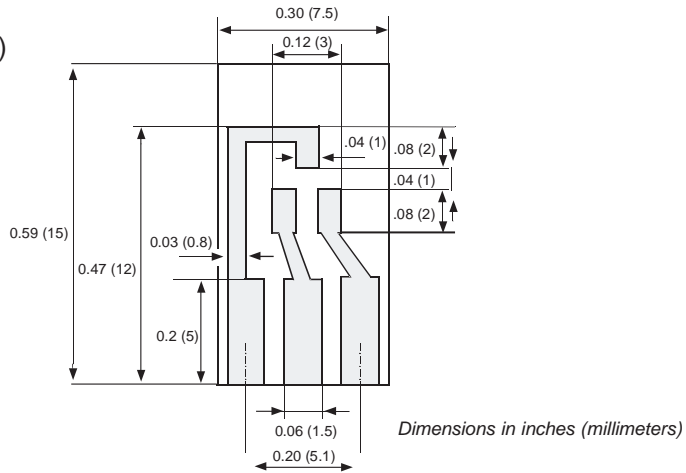
**Electrical Characteristics** ( $T_J = 25^\circ\text{C}$  unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Forward Voltage	$V_F$	$I_F = 10 \text{ mA}$	—	—	1.0	V
Leakage Current	$I_R$	$V_R = 70 \text{ V}$	—	—	2.5	$\mu\text{A}$
		$V_R = 70 \text{ V}, T_j = 150^\circ\text{C}$	—	—	50	$\mu\text{A}$
		$V_R = 25 \text{ V}, T_j = 150^\circ\text{C}$	—	—	30	$\mu\text{A}$
Capacitance	$C_{\text{tot}}$	$V_F = V_R = 0$	—	—	4	pF
Reverse Recovery Time (see figures)	$t_{\text{rr}}$	$I_F = 10 \text{ mA}, I_R = 10 \text{ mA}$ $V_R = 6 \text{ V}, R_L = 100 \Omega$	—	—	4	ns

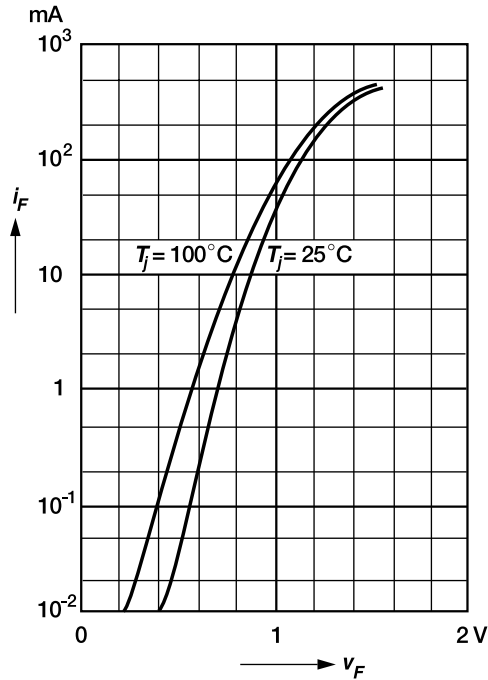
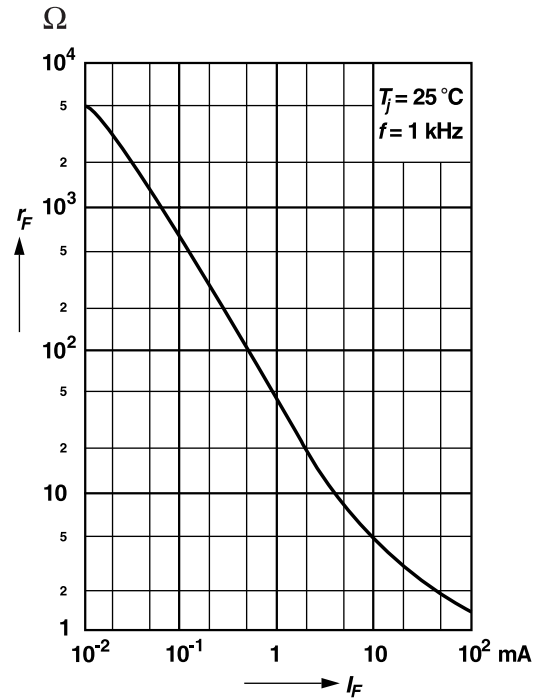
(1) Device on fiberglass substrate, see layout (SOT-23).

**Layout for  $R_{\text{thJA}}$  test**

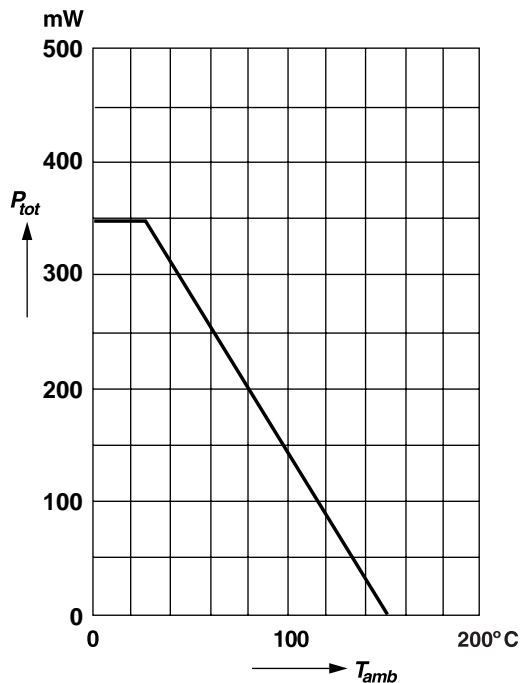
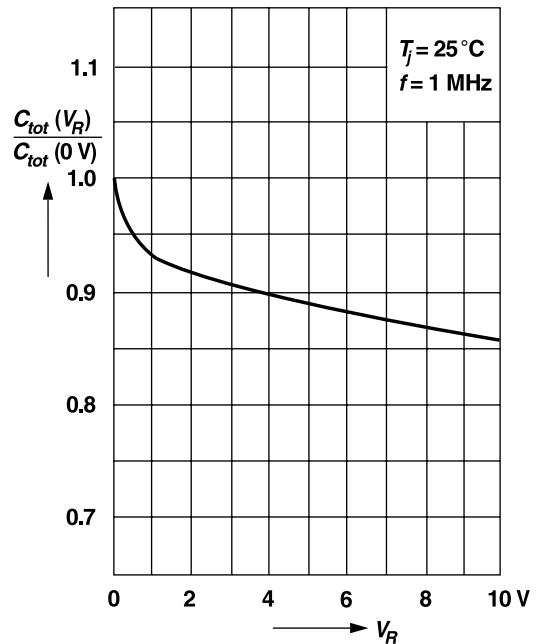
Thickness: Fiberglass 0.059 in. (1.5 mm)  
Copper leads 0.012 in. (0.3 mm)



**Ratings and Characteristic Curves** ( $T_A = 25^\circ\text{C}$  unless otherwise noted)

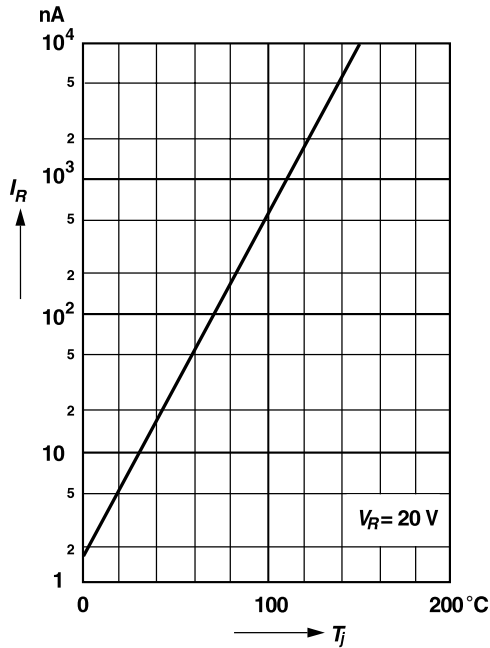
**Forward characteristics**

**Dynamic forward resistance versus forward current**

**Admissible power dissipation versus ambient temperature**

For conditions, see footnote in table "Absolute Maximum Ratings"


**Relative capacitance versus reverse voltage**


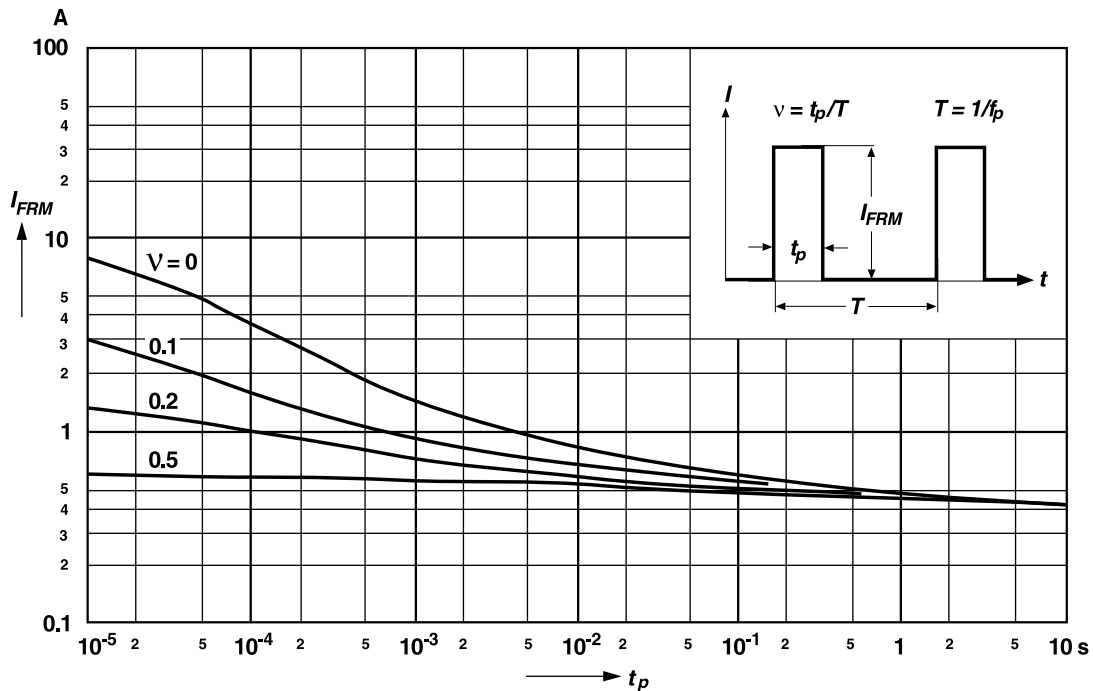
**Ratings and Characteristic Curves** ( $T_A = 25^\circ\text{C}$  unless otherwise noted)

**Leakage current versus junction temperature**



**Admissible repetitive peak forward current versus pulse duration**

For conditions, see footnote in table "Absolute Maximum Ratings"





LittleDiode supplies new, hard to find or obsolete electronic components and semiconductors all over the world.

With over two million different components listed you are sure to find the part you need.

Feel free to visit us today at our online store:

**[LittleDiode.com](http://LittleDiode.com)**

Looking forward to providing you with the best possible service.